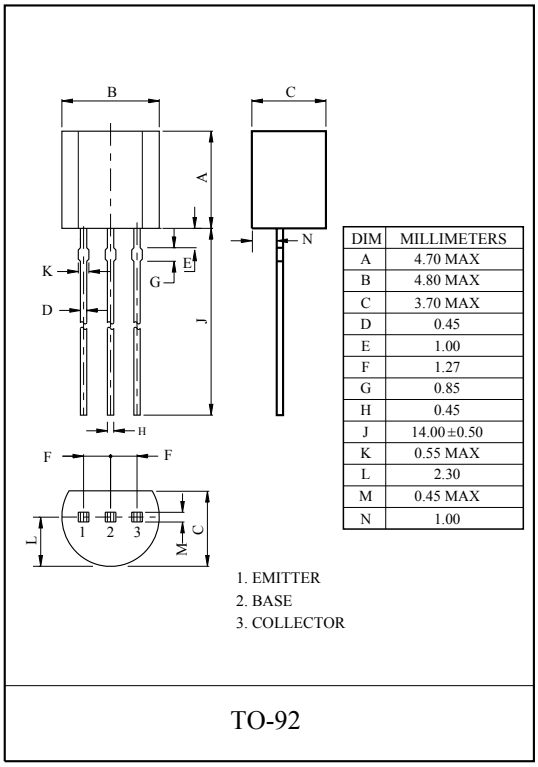
KTC8550

EPITAXIAL PLANAR PNP TRANSISTOR

HIGH CURRENT APPLICATION.

FEATURE

· Complementary to KTC8050.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

1. EMITTER
2. BASE
3. COLLECTOR

TO-92

MAXIMUM RATING (Ta=25℃)

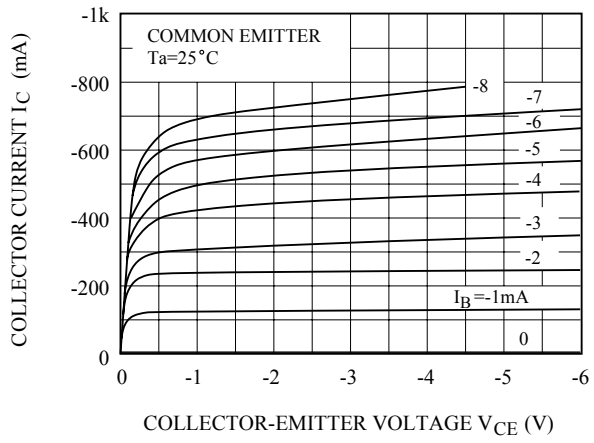
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Emitter Current	I_E	800	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

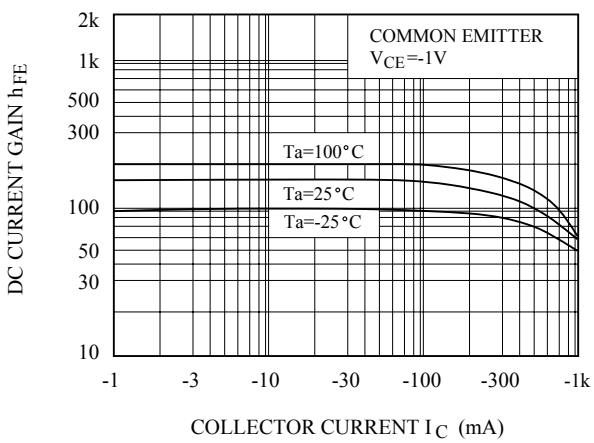
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-15V, I_E=0	-	-	-50	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-0.5mA, I_E=0	-35	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-30	-	-	V
DC Current Gain	h_{FE}(1) (Note)	V_{CE}=-1V, I_C=-50mA	100	-	300	
	h_{FE}(2)	V_{CE}=-1V, I_C=-350mA	60	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA	-	-	-0.5	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-1V, I_C=-500mA	-	-	-1.2	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-10mA	-	120	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, f=1MHz, I_E=0	-	19	-	pF

Note : h_{FE}(1) Classification C : 100～200, D : 150～300

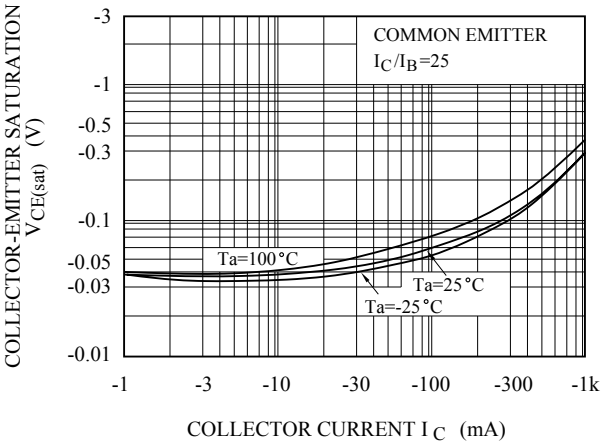
I_C - V_{CE}



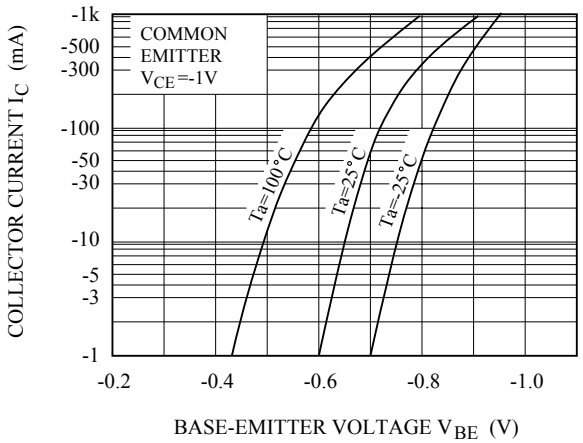
h_{FE} - I_C



$V_{CE(sat)}$ - I_C



I_C - V_{BE}



Pc - Ta